



UTV005P

0.5 Watts, 20 Volts, Class A
UHF Television - Band IV & V

GENERAL DESCRIPTION

The UTV005P is a COMMON EMITTER transistor capable of providing 0.5 Watts Peak, Class A, RF Output Power over the band 470 - 860 MHz. Gold Metalization and Diffused Ballasting are used to provide high reliability and supreme ruggedness.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation

Device Dissipation @ 25°C 8 W

Maximum Voltage and Current

Collector to Base Voltage (BV_{ces}) 45 V

Emitter to Base Voltage (BV_{ebo}) 4.0 V

Collector to Emitter Voltage (BV_{ceo}) 3.5 V

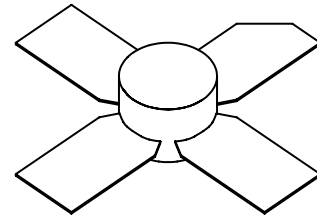
Collector Current (I_c) 750 mA

Maximum Temperatures

Storage Temperature -65 to +150 °C

Operating Junction Temperature +200 °C

CASE OUTLINE 55FU-1



ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P_{out}	Power Output – Peak synch	F = 470-860 MHz V_{cc} = 20 Volts I_c = 220 mA P_{ref} = 0.5 W F = 860 MHz	0.5			W
P_{in}	Power Input				50	mW
P_g	Power Gain			11		dB
IMD	Intermodulation Distortion			-60		dBc
VSWR	Load Mismatch Tolerance				10:1	

FUNCTIONAL CHARACTERISTICS @ 25°C

BV_{ceo}	Emitter to Base Breakdown	I_e = 20 mA	24			V
BV_{ces}	Collector to Emitter Breakdown	I_c = 10 mA	45			V
BV_{ebo}	Emitter to Base Breakdown	I_e = 1 mA	3.5			V
h_{FE}	DC – Current Gain	V_{ce} = 5V, I_c = 100 mA	20			
C_{ob}	Capacitance			5.0		pF
θ_{jc}^1	Thermal Resistance				22	°C/W

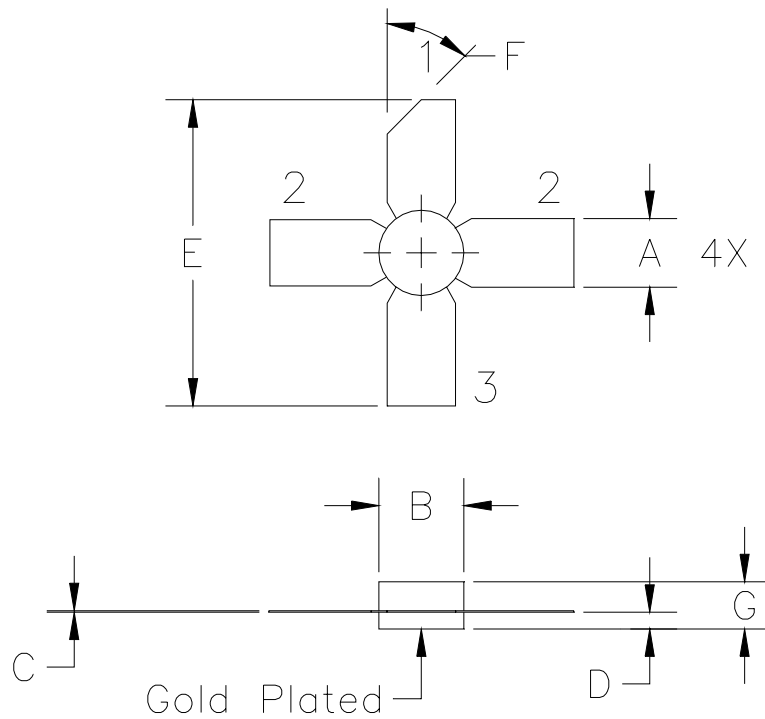
Note 1: F1=860 MHz, F2=863.5 MHz, F3=864.5 MHz

European test method, Vision = - 8dB, Sideband= - 16dB, Sound = -7 dB

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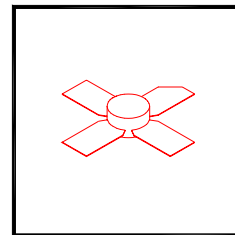
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1002MP

STYLE 1:
 PIN1 = COLLECTOR
 2 = BASE (2X)
 3 = EMITTER

STYLE 2:
 PIN1 = COLLECTOR
 2 = EMITTER (2X)
 3 = BASE

DIM	MILLIMETER	±TOL	INCHES	±TOL
A	5.71	.13	.225	.005
B	7.11 DIA	.13	.280 DIA	.005
C	0.13	.02	.005	.001
D	1.40	.13	.055	.005
E	25.53	.64	1.005	.025
F	45°	5°	45°	5°
G	3.94	REF	.155	REF



GHZ TECHNOLOGY
 RF - MICROWAVE SILICON POWER TRANSISTORS

DWG NO.

55FU